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# **FDG6335N**

# 20V N-Channel PowerTrench® MOSFET

## **General Description**

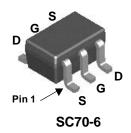
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized use in small switching regulators, providing an extremely low  $R_{\text{DS}(\text{ON})}$  and gate charge  $(Q_{\text{G}})$  in a small package.

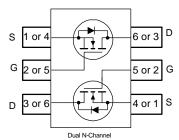
## **Applications**

- DC/DC converter
- · Power management
- Loadswitch

#### **Features**

- 0.7 A, 20 V.  $R_{DS(ON)} = 300 \text{ m}\Omega \ @ \ V_{GS} = 4.5 \text{ V}$   $R_{DS(ON)} = 400 \text{ m}\Omega \ @ \ V_{GS} = 2.5 \text{ V}$
- Low gate charge (1.1 nC typical)
- High performance trench technology for extremely low  $R_{\mbox{\scriptsize DS(ON)}}$
- Compact industry standard SC70-6 surface mount package





The pinouts are symmetrical; pin 1 and pin 4 are interchangeable.

# Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

| Symbol                            | Parameter  |          | Ratings     | Units |
|-----------------------------------|--|----------|-------------|-------|
| $V_{DSS}$                         | Drain-Source Voltage                             |          | 20          | V     |
| V <sub>GSS</sub>                  | Gate-Source Voltage                              |          | ± 12        | V     |
| I <sub>D</sub>                    | Drain Current - Continuous                       | (Note 1) | 0.7         | А     |
|                                   | - Pulsed   |          | 2.1         |       |
| P <sub>D</sub>                    | Power Dissipation for Single Operation           | (Note 1) | 0.3         | W     |
| T <sub>J</sub> , T <sub>STG</sub> | Operating and Storage Junction Temperature Range |          | -55 to +150 | °C    |

## **Thermal Characteristics**

| $R_{\theta JA}$ | Thermal Resistance, Junction-to-Ambient | (Note 1) | 415 | °C/W |
|-----------------|---|----------|-----|------|
|-----------------|---|----------|-----|------|

**Package Marking and Ordering Information** 

| Device Marking | Device   | Reel Size | Tape width | Quantity   |
|----------------|----------|-----------|------------|------------|
| .35            | FDG6335N | 7"        | 8mm        | 3000 units |

| Symbol                               | Parameter   | Test Conditions  | Min | Тур               | Max               | Units |
|--------------------------------------|---|--|-----|-------------------|-------------------|-------|
| Off Char                             | acteristics                                       |  | II. |                   |                   | l     |
| BV <sub>DSS</sub>                    | Drain–Source Breakdown<br>Voltage                 | $V_{GS} = 0 \text{ V}, \qquad I_D = 250  \mu\text{A}$  | 20  |                   |                   | V     |
| $\Delta BV_{DSS} \over \Delta T_{J}$ | Breakdown Voltage Temperature Coefficient         | $I_D$ = 250 $\mu$ A, Referenced to 25°C  |     | 14                |                   | mV/°C |
| I <sub>DSS</sub>                     | Zero Gate Voltage Drain Current                   | V <sub>DS</sub> = 16 V, V <sub>GS</sub> = 0 V  |     |                   | 1                 | μΑ    |
| I <sub>GSSF</sub>                    | Gate-Body Leakage, Forward                        | $V_{GS} = 12 \text{ V},  V_{DS} = 0 \text{ V}$   |     |                   | 100               | nA    |
| I <sub>GSSR</sub>                    | Gate-Body Leakage, Reverse                        | $V_{GS} = -12 \text{ V},  V_{DS} = 0 \text{ V}$  |     |                   | -100              | nA    |
| On Chara                             | acteristics (Note 2)                              |  | •   |                   | •                 |       |
| $V_{GS(th)}$                         | Gate Threshold Voltage                            | $V_{DS} = V_{GS}$ , $I_D = 250 \mu\text{A}$  | 0.6 | 1.1               | 1.5               | V     |
| $\Delta V_{GS(th)} \over \Delta T_J$ | Gate Threshold Voltage<br>Temperature Coefficient | $I_D = -250 \mu A$ , Referenced to 25°C  |     | -2.8              |                   | mV/°C |
| R <sub>DS(on)</sub>                  | Static Drain–Source<br>On–Resistance              | $ \begin{array}{cccccccccccccccccccccccccccccccccccc$  |     | 180<br>293<br>247 | 300<br>400<br>442 | mΩ    |
| I <sub>D(on)</sub>                   | On-State Drain Current                            | $V_{GS} = 4.5 \text{ V},  I_D = 0.7 \text{ A}, T_J=125^{\circ}\text{C}$<br>$V_{GS} = 4.5 \text{ V},  V_{DS} = 5 \text{ V}$ | 1   |                   |                   | Α     |
| <b>g</b> FS                          | Forward Transconductance                          | $V_{DS} = 5 \text{ V}, \qquad I_{D} = 0.7 \text{ A}$   |     | 2.8               |                   | S     |
| Dynamic                              | Characteristics                                   |  |     |                   |                   |       |
| C <sub>iss</sub>                     | Input Capacitance                                 | V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V,   |     | 113               |                   | pF    |
| Coss                                 | Output Capacitance                                | f = 1.0 MHz  |     | 34                |                   | pF    |
| C <sub>rss</sub>                     | Reverse Transfer Capacitance                      |  |     | 16                |                   | pF    |
| Switching                            | Characteristics (Note 2)                          |  |     |                   |                   |       |
| t <sub>d(on)</sub>                   | Turn-On Delay Time                                | $V_{DD} = 10 \text{ V},  I_D = 1 \text{ A},$   |     | 5                 | 10                | ns    |
| t <sub>r</sub>                       | Turn-On Rise Time                                 | $V_{GS} = 4.5 \text{ V}, R_{GEN} = 6 \Omega$   |     | 7                 | 15                | ns    |
| t <sub>d(off)</sub>                  | Turn-Off Delay Time                               |  |     | 9                 | 18                | ns    |
| t <sub>f</sub>                       | Turn-Off Fall Time                                |  |     | 1.5               | 3                 | ns    |
| $Q_g$                                | Total Gate Charge                                 | $V_{DS} = 10 \text{ V},  I_{D} = 0.7 \text{ A},$   |     | 1.1               | 1.4               | nC    |
| Q <sub>gs</sub>                      | Gate-Source Charge                                | V <sub>GS</sub> = 4.5 V  |     | 0.24              |                   | nC    |
| $Q_{gd}$                             | Gate-Drain Charge                                 |  |     | 0.3               |                   | nC    |
| Drain-Sc                             | ource Diode Characteristics                       | and Maximum Ratings  |     |                   |                   |       |
| Is                                   | Maximum Continuous Drain-Sour                     | <u> </u>   |     |                   | 0.25              | Α     |
| $V_{SD}$                             | Drain–Source Diode Forward<br>Voltage             | $V_{GS} = 0 \text{ V}, \qquad I_S = 0.25 \text{ A} \text{ (Note 2)}$   |     | 0.74              | 1.2               | V     |

#### Notes

<sup>1.</sup>  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta JA}$  is determined by the user's board design.  $R_{\theta JA} = 415^{\circ}\text{C/W}$  when mounted on a minimum pad.

<sup>2.</sup> Pulse Test: Pulse Width < 300µs, Duty Cycle < 2.0%

# **Typical Characteristics**

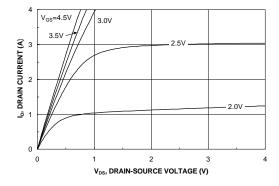


Figure 1. On-Region Characteristics.

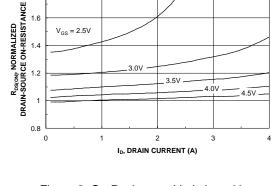


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

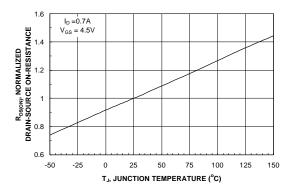


Figure 3. On-Resistance Variation with Temperature.

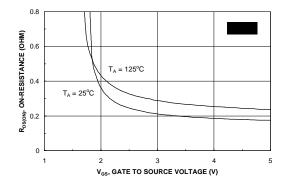


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

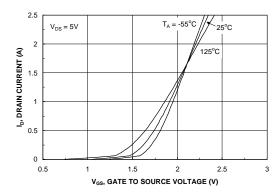


Figure 5. Transfer Characteristics.

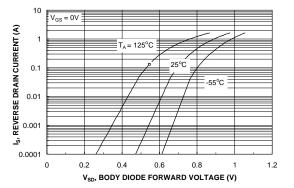
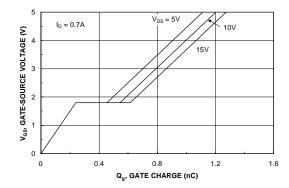


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

# **Typical Characteristics**



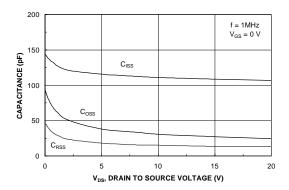
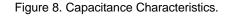
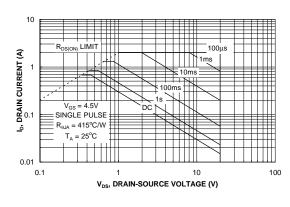


Figure 7. Gate Charge Characteristics.





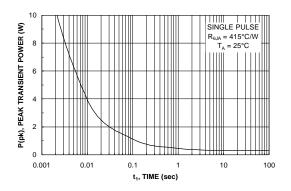


Figure 9. Maximum Safe Operating Area.



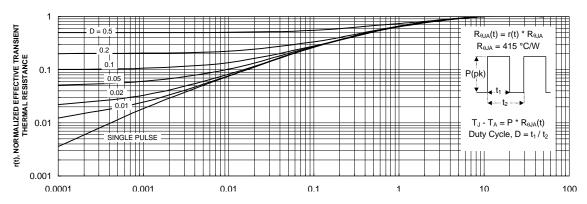


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1. Transient thermal response will change depending on the circuit board design.

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